MITSUBISHI ELECTRIC

TENTATIVE
Notice: This is not a final specification.
Some parametric limits are subject to change

<Intelligent Power Modules>

PM50RGB120

FLAT-BASE TYPE
INSULATED PACKAGE

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Approved by		H. Takemoto
(Date)		8th-Oct. 2015

FEATURE

a) Adopting Full-Gate CSTBT™ chip.

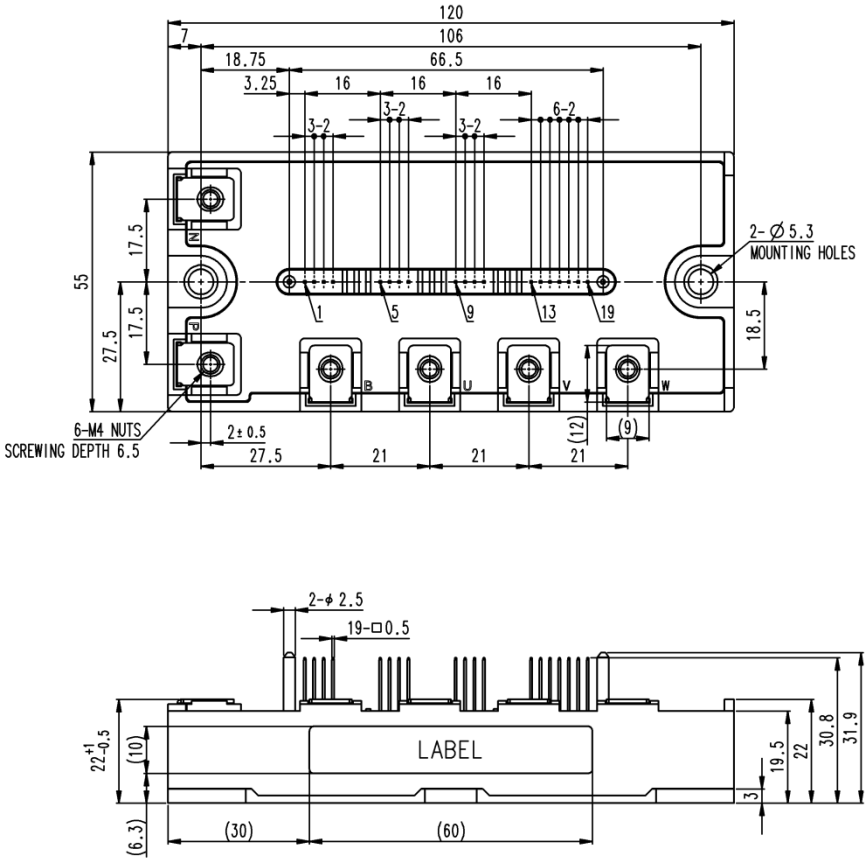
b) The over-temperature protection which detects the chip surface temperature of CSTBT™ is adopted.

c) Error output signal is possible from all each protection upper and lower arm of IPM.

APPLICATION

General purpose inverter, servo drives and other motor controls

PACKAGE OUTLINES **Dimensions in mm**



1. VUPC
2. UFO
3. UP
4. VUP1
5. VVPC
6. VFO
7. VP
8. VVP1
9. VWPC
10. WFO
11. WP
12. VWP1
13. VNC
14. VN1
15. Br
16. UN
17. VN
18. WN
19. Fo

PM50RGB120

HIGH POWER SWITCHING USE
INSULATED TYPE

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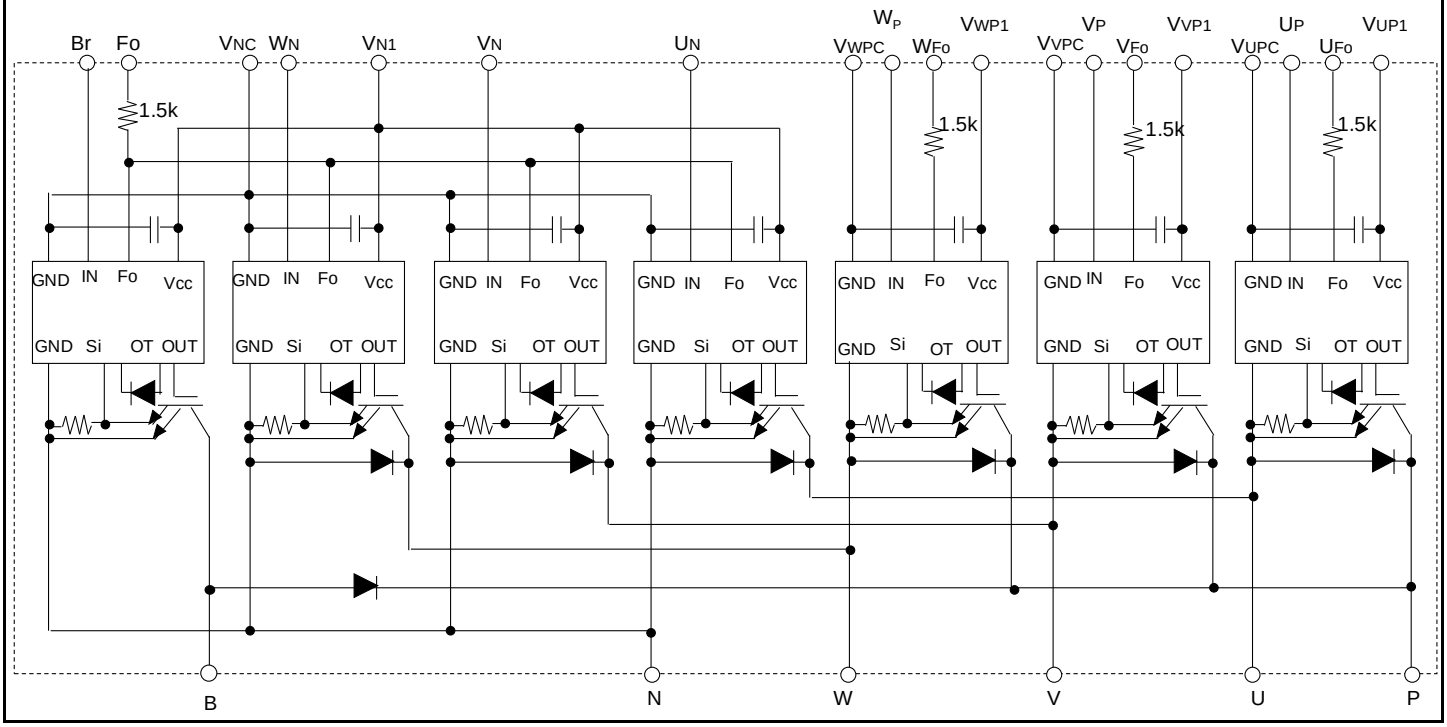
INTERNAL FUNCTIONS BLOCK DIAGRAM



MAXIMUM RATINGS (T_j = 25°C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	V_D=15 V, V_{CIN}=15 V	1200	V
I_C	Collector Current	T_C=25 °C	50	A
I_{CRM}		Pulse	100	
P_{tot}	Total Power Dissipation	T_C=25 °C	431	W
I_E	Emitter Current	T_C=25 °C	50	A
I_{ERM}	(Free-wheeling Diode Forward current)	Pulse	100	
T_j	Junction Temperature		-20 ~ +150	°C

*: Tc measurement point is just under the chip.

BRAKE PART

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	V_D=15 V, V_{CIN}=15 V	1200	V
I_C	Collector Current	T_C=25 °C	25	A
I_{CRM}		Pulse	50	
P_{tot}	Total Power Dissipation	T_C=25 °C	297	W
$V_{R(DC)}$	Diode Rated Reverse DC Voltage	T_C=25 °C	1200	V
I_F	Diode Forward Current	T_C=25 °C	25	A
T_j	Junction Temperature		-20 ~ +150	°C

*: Tc measurement point is just under the chip.

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CONTROL PART

Symbol	Parameter	Conditions	Ratings	Unit
V_D	Supply Voltage	Applied between: V_{UP1}-V_{UPC}, V_{VP1}-V_{VPC}, V_{WP1}-V_{WPC}, V_{N1}-V_{NC}	20	V
V_{CIN}	Input Voltage	Applied between: U_P-V_{UPC}, V_P-V_{VPC}, W_P-V_{WPC}, U_N, V_N, W_N, Br-V_{NC}	20	V
V_{FO}	Fault Output Supply Voltage	Applied between: U_{FO}-V_{UPC}, V_{FO}-V_{VPC}, W_{FO}-V_{WPC}, Fo-V_{NC}	20	V
I_{FO}	Fault Output Current	Sink current at U_{FO}, V_{FO}, W_{FO}, Fo terminals	20	mA

TOTAL SYSTEM

Symbol	Parameter	Conditions	Ratings	Unit
$V_{CC(PROT)}$	Supply Voltage Protected by SC	V_D =13.5 V~16.5 V, Inverter Part, T_j=+125°C start	800	V
$V_{CC(surge)}$	Supply Voltage (Surge)	Applied between: P-N, Surge value	1000	V
T_{stg}	Storage Temperature	-	-40 ~ +125	°C
V_{isol}	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base plate, AC 1min, RMS	2500	V

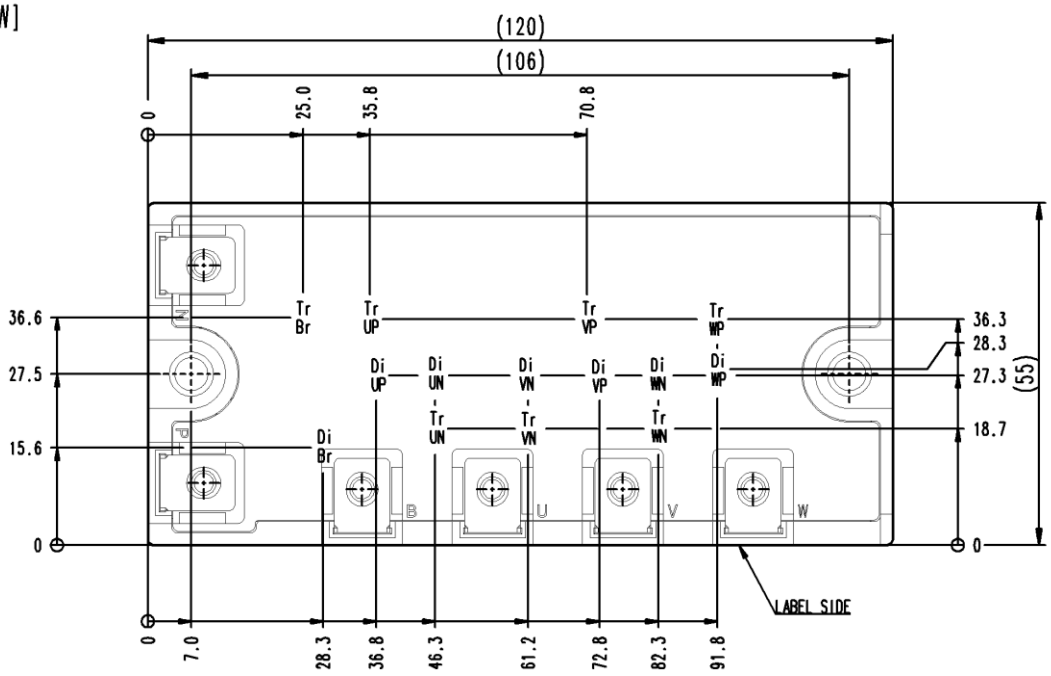
*: Tc measurement point is just under the chip.

THERMAL RESISTANCE

Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal Resistance	Inverter, Junction to case, IGBT, per 1 element (Note1)	-	-	0.29	K/W
$R_{th(j-c)D}$		Inverter, Junction to case, FWD, per 1 element (Note1)	-	-	0.46	
$R_{th(j-c)Q}$		Brake, Junction to case, IGBT, per 1 element (Note1)	-	-	0.42	
$R_{th(j-c)D}$		Brake, Junction to case, Diode, per 1 element (Note1)	-	-	0.57	
$R_{th(c-s)}$	Contact Thermal Resistance	Case to heat sink, per 1 module, Thermal grease applied (Note.1)	-	0.022	-	

Note1. If you use this value, $R_{th(s-a)}$ should be measured just under the chips.

[TOP VIEW]



ELECTRICAL CHARACTERISTICS (T_j= 25°C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Conditions		Limits			Unit
				Min.	Typ.	Max.	
V_{CEsat}	Collector-Emitter Saturation Voltage	V_D=15 V, I_C=50A	T_j=25 °C	-	1.65	2.15	V
		V_{CIN}=0 V, Pulsed, Terminal (Fig.1)	T_j=125 °C	-	1.85	2.35	
V_{EC}	Emitter-Collector Voltage	I_E=50 A, V_D=15 V, V_{CIN}= 15 V, Terminal (Fig.2)		-	2.00	3.00	V
t_{on}	Switching Time	V_D=15 V, V_{CIN}=0 V⟷15 V,		-	0.6	-	μs
t_{rr}		V_{CC}=300 V, I_C=50A,		-	0.2	-	
$t_{c(on)}$		T_j=125 °C,		-	0.2	-	
t_{off}		Inductive Load		-	1.1	-	
$t_{c(off)}$		(Fig.3, 4)		-	0.4	-	
I_{CES}	Collector-Emitter Cut-off Current	V_{CE}=V_{CES}, V_D=15 V, V_{CIN}=15 V (Fig.5)	T_j=25 °C	-	-	1	mA
			T_j=125 °C	-	-	10	

BRAKE PART

Symbol	Parameter	Conditions		Limits			Unit
				Min.	Typ.	Max.	
V_{CEsat}	Collector-Emitter Saturation Voltage	V_D=15 V, I_C=25A	T_j=25 °C	-	1.65	2.15	V
		V_{CIN}=0 V, Pulsed, Terminal (Fig.1)	T_j=125 °C	-	1.85	2.35	
V_{FM}	Diode Forward Voltage	I_F=25A		-	1.80	2.75	V
I_{CES}	Collector-Emitter Cut-off Current	V_{CE}=V_{CES}, V_D=15 V, V_{CIN}=15 V (Fig.5)	T_j=25 °C	-	-	1	mA
			T_j=125 °C	-	-	10	

CONTROL PART

Symbol	Parameter	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I_D	Circuit Current	V_D=15 V, V_{CIN}=15 V	V_{P1}-V_{PC}	-	2	4	mA
			V_{N1}-V_{NC}	-	8	16	
$V_{th(ON)}$	Input ON Threshold Voltage	Applied between:		1.2	1.5	1.8	V
$V_{th(OFF)}$	Input OFF Threshold Voltage	U_P-V_{UPC}, V_P-V_{VPC}, W_P-V_{WPC}, U_N, V_N, W_N, Br-V_{NC}		1.7	2.0	2.3	
SC	Short Circuit Trip Level	-20≤T_j≤125 °C, V_D=15 V (Fig.3, 6)	Inverter	100	-	-	A
			Brake	50	-	-	
$t_{off(SC)}$	Short Circuit Current Delay Time	V_D=15 V (Fig.3, 6)		-	0.2	-	μs
OT	Over Temperature Protection	Detect Temperature of IGBT chip	Trip level	150	-	-	°C
$OT_{(hys)}$			Hysteresis	-	20	-	
UV_t	Supply Circuit Under-Voltage Protection	-20≤T_j≤125 °C	Trip level	11.5	12.0	12.5	V
UV_r			Reset level	-	12.5	-	
$I_{FO(H)}$	Fault Output Current	V_D=15 V, V_{FO}=15 V (Note2)		-	-	0.01	mA
$I_{FO(L)}$				-	10	15	
t_{FO}	Fault Output Pulse Width	V_D=15 V (Note2)		1.0	1.8	-	ms

Note2. Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

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MECHANICAL RATINGS AND CHARACTERISTICS

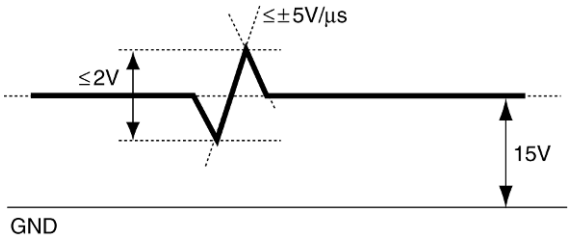
Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_s	Mounting Torque	Mounting part screw : M5	2.5	3.0	3.5	N•m
M_t	Mounting Torque	Main terminal part screw : M4	1.5	1.7	2.0	N•m
m	mass	-	-	320	-	g

RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Conditions	Recommended value	Unit
V_{CC}	Supply Voltage	Applied across P-N terminals	≤ 800	V
V_D	Control Supply Voltage	Applied between : V_{UP1}-V_{UPC}, V_{VP1}-V_{VPC}, V_{WP1}-V_{WPC}, V_{N1}-V_{NC} (Note3)	15.0±1.5	V
$V_{CIN(ON)}$	Input ON Voltage	Applied between : U_P-V_{UPC}, V_P-V_{VPC}, W_P-V_{WPC}, U_N, V_N, W_N, Br-V_{NC}	≤ 0.8	V
$V_{CIN(OFF)}$	Input OFF Voltage		≥ 9.0	
f_{PWM}	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
t_{dead}	Dead Time	For IPM's each input signals (Fig.7)	≥ 2.5	μs

This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note3. With ripple satisfying the following conditions: dv/dt swing ≤ ±5 V/μs, Variation ≤ 2 V peak to peak



PRECAUTIONS FOR TESTING

1. Before applying any control supply voltage (V_D), the input terminals should be pulled up by resistors, etc. to their corresponding supply voltage and each input signal should be kept off state.
   After this, the specified ON and OFF level setting for each input signal should be done.
2. When performing “SC” tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above V_{CES} rating of the device.
   (These test should not be done by using a curve tracer or its equivalent.)

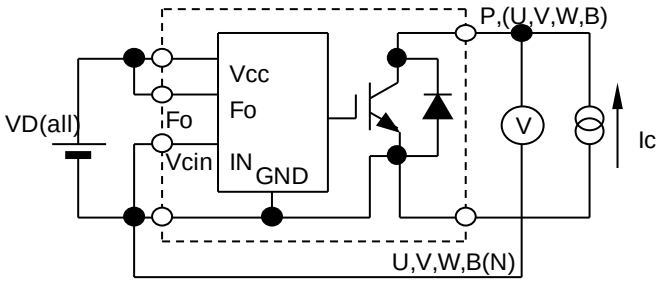


Fig.1 V_{CEsat} Test

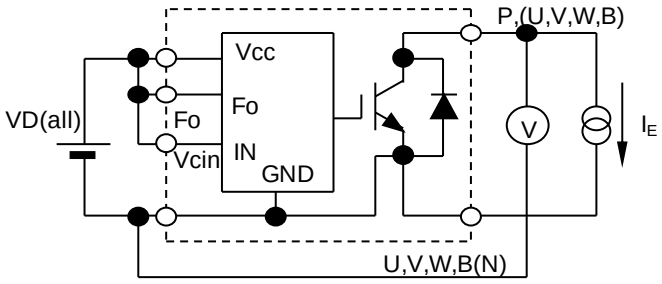


Fig.2 V_{EC} Test

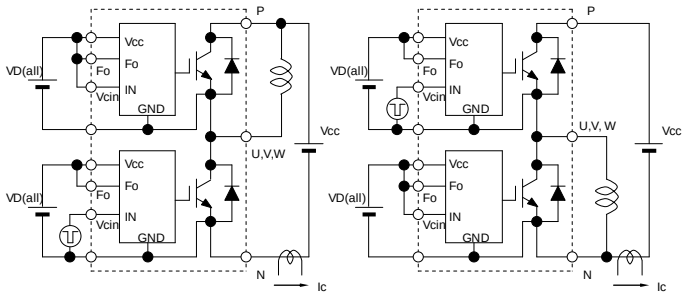


Fig.3 Switching time and SC test circuit

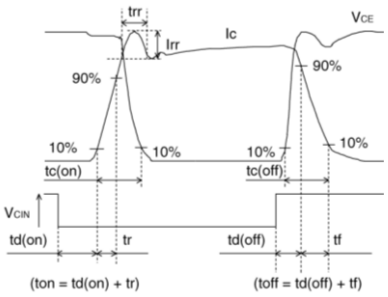


Fig.4 Switching time test waveform

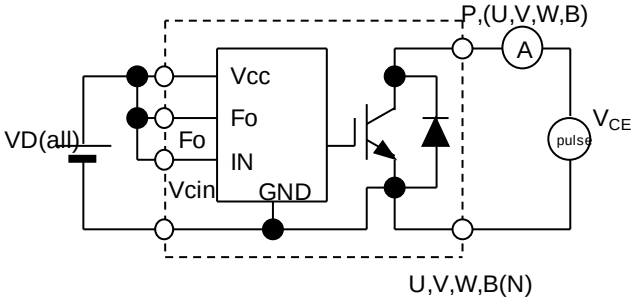


Fig.5 I_{CES} Test

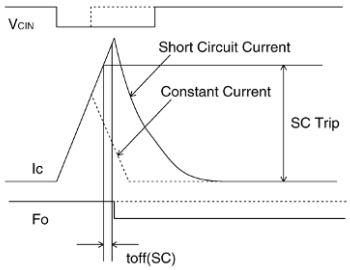
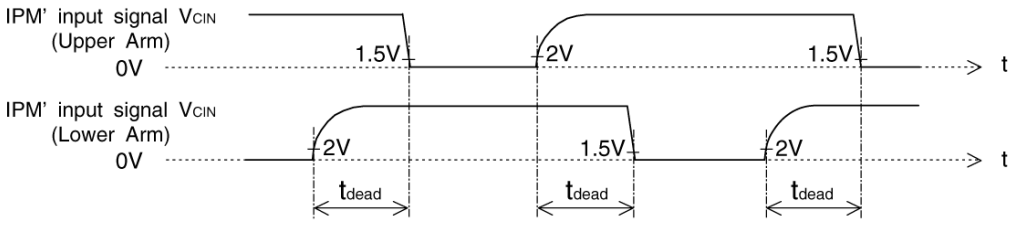


Fig.6 SC test waveform



1.5V: Input on threshold voltage Vth(on) typical value, 2V: Input off threshold voltage Vth(off) typical value

Fig. 7 Dead time measurement point example

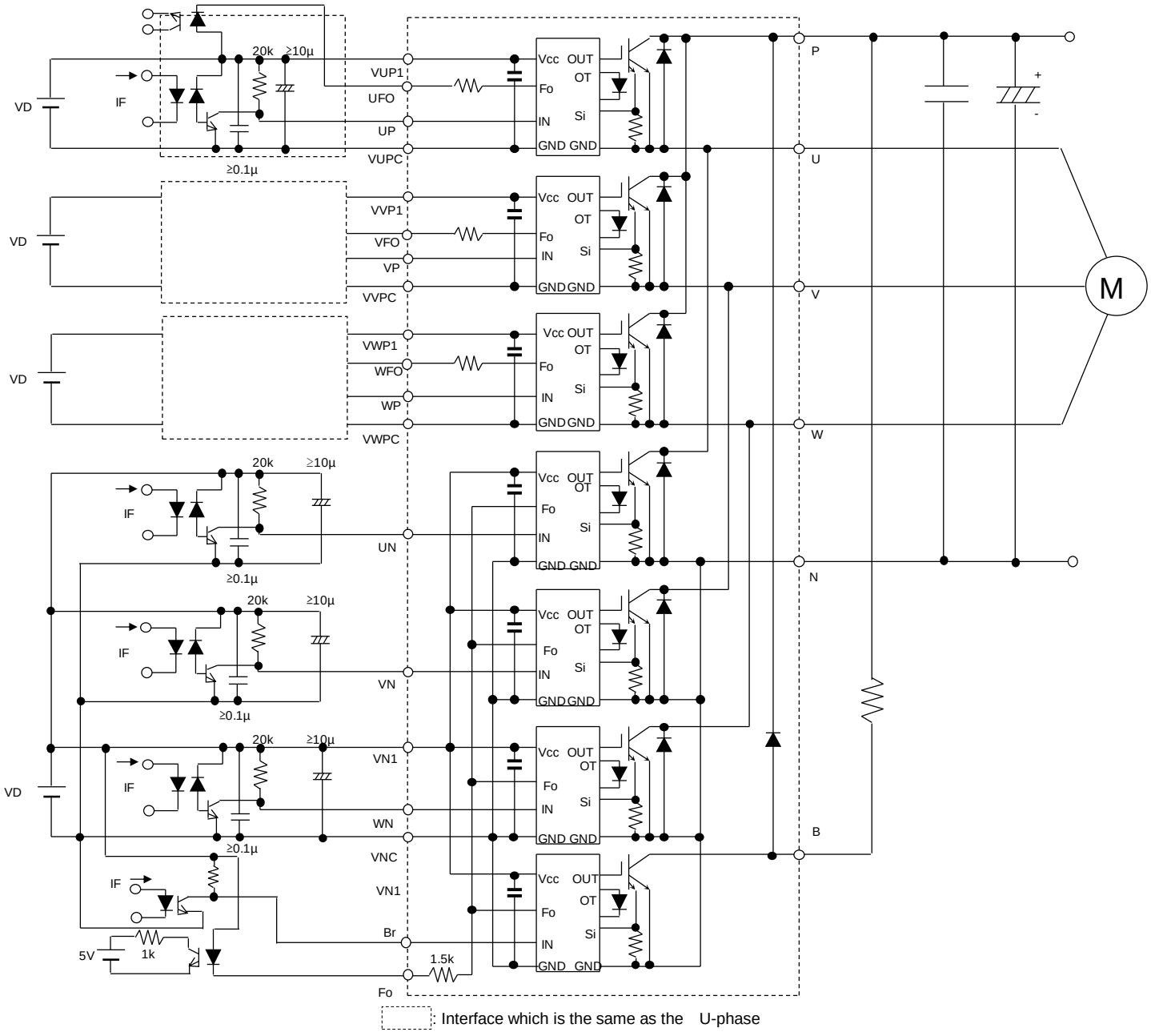


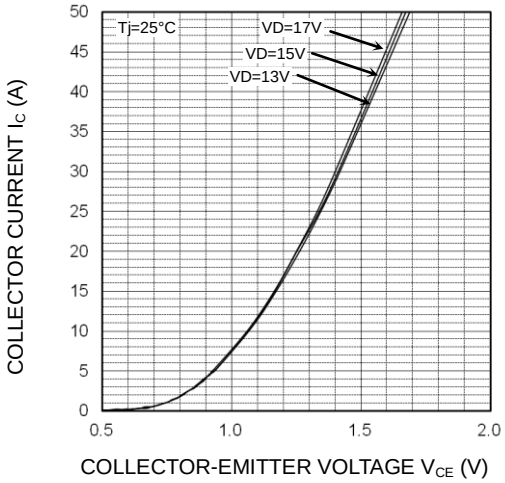
Fig. 8 Application Example Circuit

NOTES FOR STABLE AND SAFE OPERATION ;

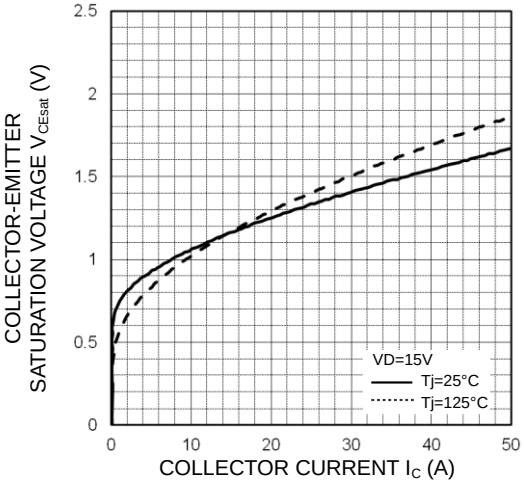
- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers: t_{PLH}, t_{PHL} ≤ 0.8μs, Use High CMR type.
- Slow switching opto-coupler: CTR > 100%
- Use 4 isolated control power supplies (V_D). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.

PERFORMANCE CURVES
(Inverter Part)

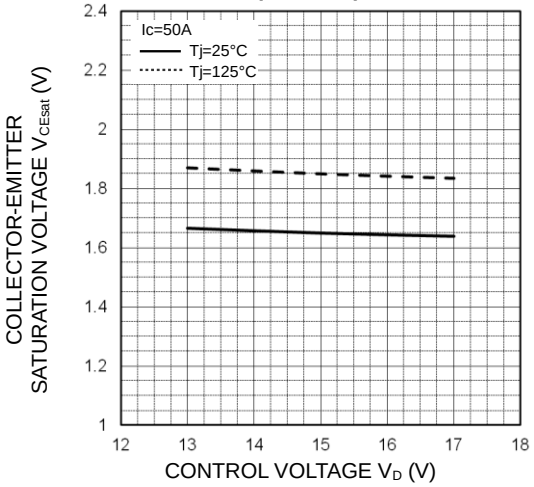
OUTPUT CHARACTERISTICS (TYPICAL)



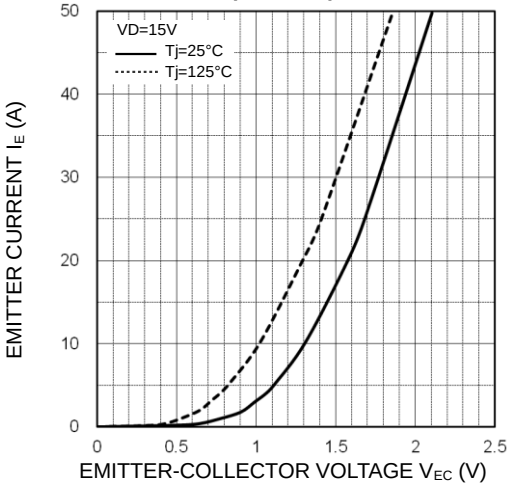
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. Ic) CHARACTERISTICS (TYPICAL)



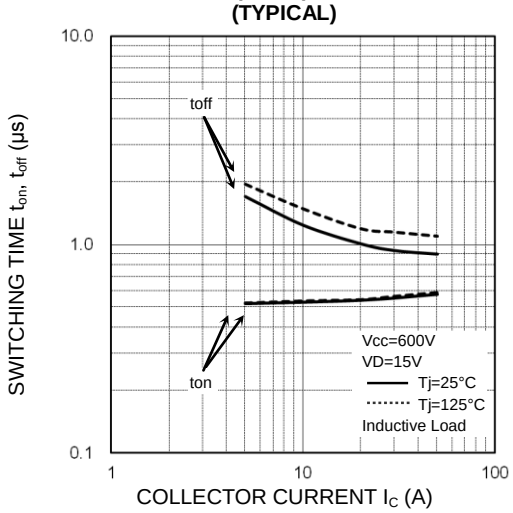
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. V_D) CHARACTERISTICS (TYPICAL)



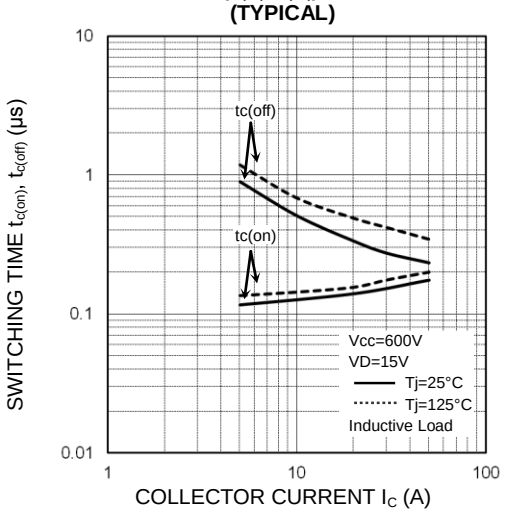
FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)



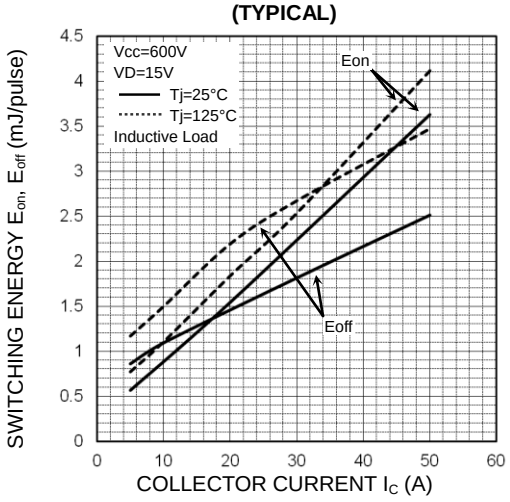
SWITCHING TIME (t_{on}, t_{off}) CHARACTERISTICS (TYPICAL)



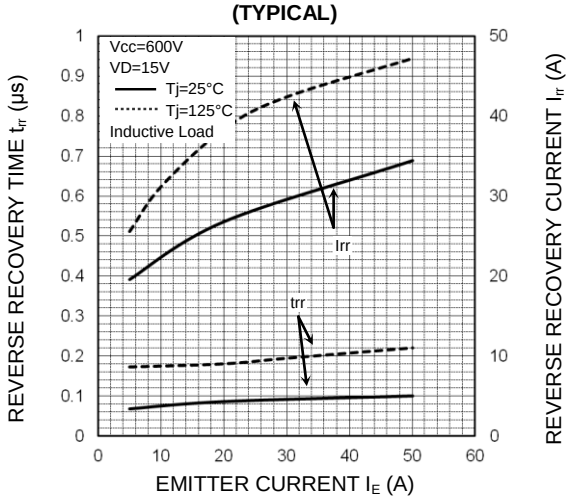
SWITCHING TIME($t_{c(on)}$, $t_{c(off)}$)CHARACTERISTICS (TYPICAL)



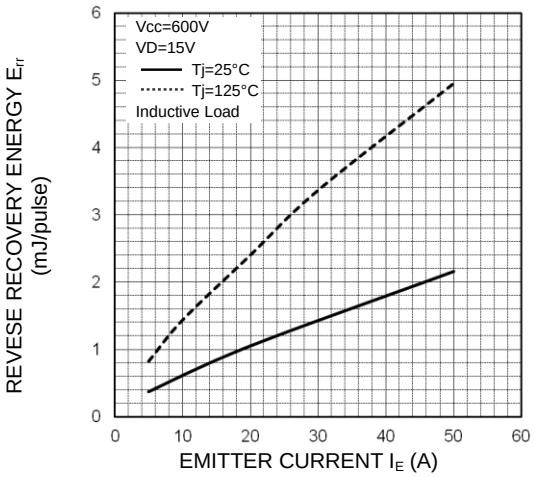
SWITCHING ENERGY CHARACTERISTICS (TYPICAL)



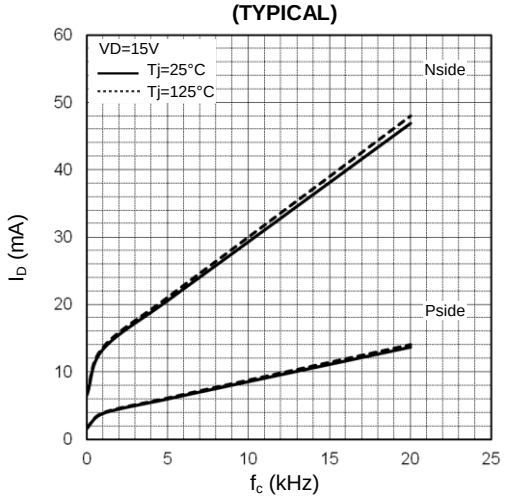
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



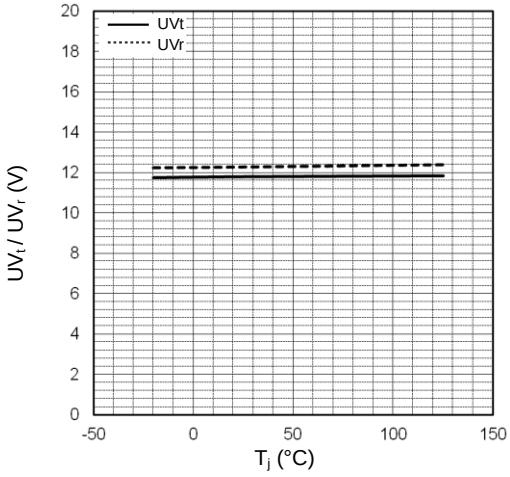
FREE WHEELING DIODE REVERSE RECOVERY ENERGY CHARACTERISTICS (TYPICAL)



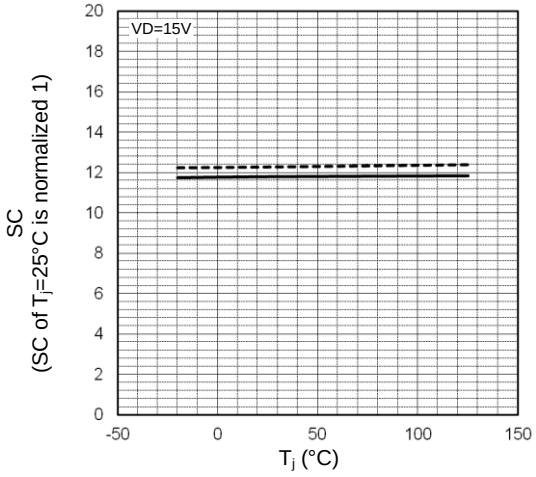
ID VS. fc CHARACTERISTICS (TYPICAL)



UV TRIP LEVEL VS. Tj CHARACTERISTICS (TYPICAL)

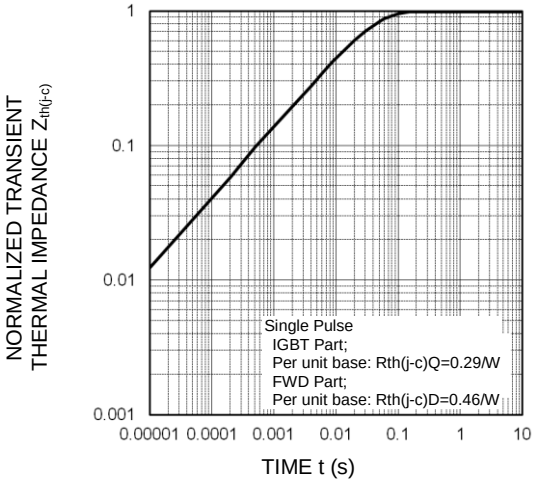


SC TRIP LEVEL VS. Tj CHARACTERISTICS (TYPICAL)

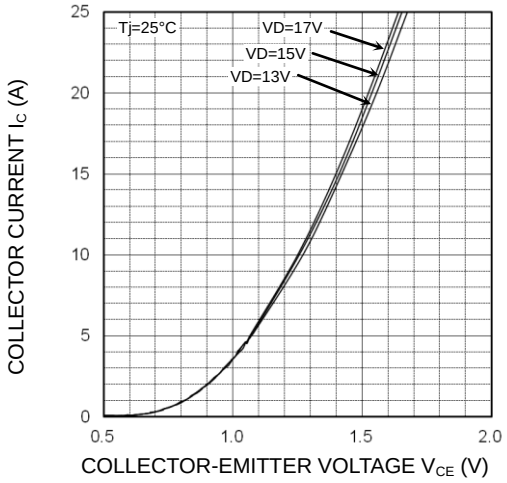


(Brake Part)

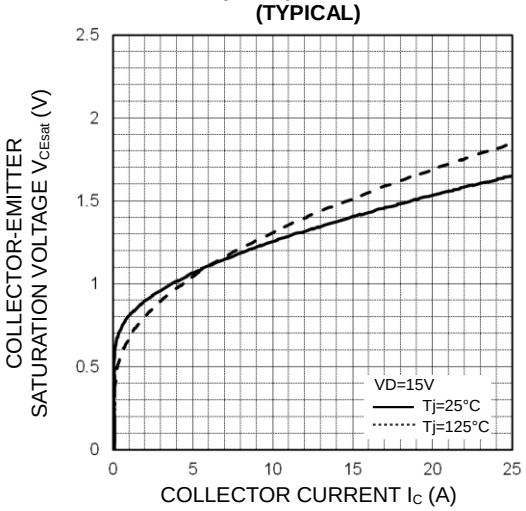
TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



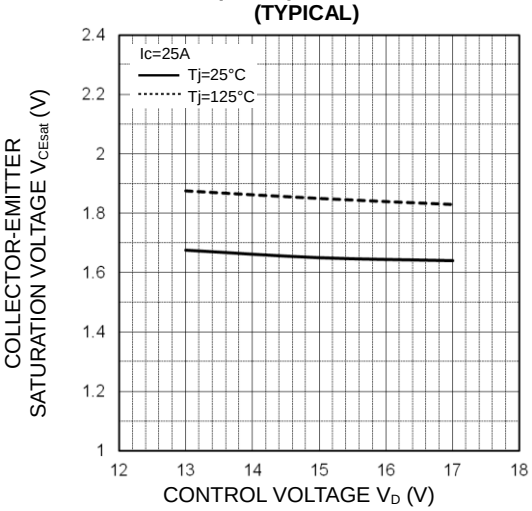
OUTPUT CHARACTERISTICS (TYPICAL)



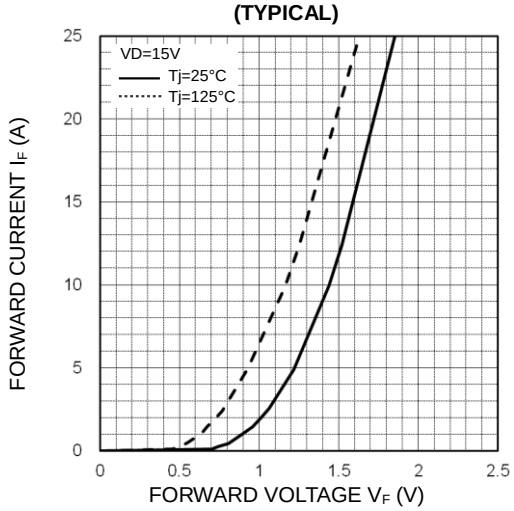
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. Ic) CHARACTERISTICS (TYPICAL)



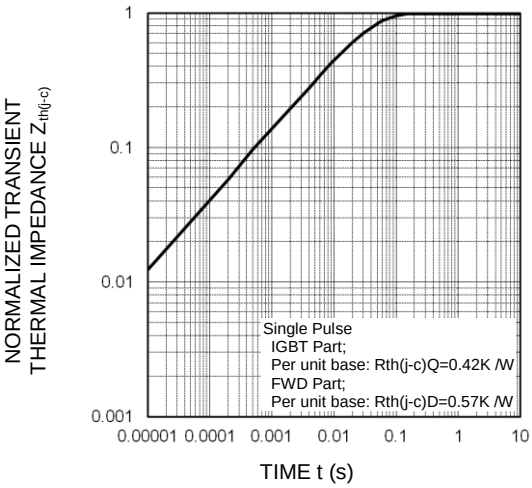
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. V_D) CHARACTERISTICS (TYPICAL)



DIODE FORWARD CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

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